an electrode for supplying an electric energy inside the vacuum chamber;

a supporting means for supporting a substrate so that a surface of said substrate is opposed to the electrode,

wherein an introducing port for introducing said gas is located adjacent to said surface of the substrate,

wherein a surface of the electrode opposing the substrate is provided with a plurality of openings,

wherein the gas is exhausted from the plurality of openings to the outside of the vacuum chamber.

Please add the following new claims 9-19.

9. The apparatus according to claim 1 wherein said substrate is located horizontally and said surface downward to the electrode.

10. An apparatus comprising:

a chamber;

a first electrode in the chamber;

a second electrode in the chamber;

a substrate holder to hold a substrate between the first and second electrode;

at least one gas inlet port to introduce a gas to a space between the substrate and the second electrode; and

a plurality of gas exhaust ports provided in said second electrode through which said gas is exhausted from said space.

11. The apparatus according to claim 10 wherein said first electrode is grounded.

12. The apparatus according to claim 10 wherein said second electrode is located below said first electrode.

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13. The apparatus according to claim 10 wherein said apparatus is a film formation apparatus.

14. The apparatus according to claim 10 wherein said gas inlet port is located in a position between the substrate and the second electrode.

15. A method comprising:

providing a first electrode and a second electrode opposed to said first electrode in a chamber wherein said second electrode is provided with a plurality of openings;

disposing a substrate between said first electrode and said second electrode;

introducing a gas into said chamber through a gas introducing port;

applying an electrical energy between the first and second electrodes to produce a plasma of said gas; and

exhausting said gas from said chamber through said plurality of openings of the second electrode.

16. The method according to claim 15 further comprising a step of moving said substrate with respect to said first and second electrode s during the application of said electrical energy.

17. The method according to claim 15 wherein said second electrode is located below said first electrode.

18. The method according to claim 15 wherein said gas introducing port is located in a position between the substrate and the second electrode.

19. The method according to claim 15 further comprising a step of forming a film on said substrate by plasma CVD from said plasma.